

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L3	16	MRAM and (magneto-resistance adj2 element\$1) and (transistor\$1 with parallel) and ("same" with state)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/10 11:20
L8	1	("5355341").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/10/10 10:51
L9	5	MRAM and (magneto-resistance adj2 element\$1) and (transistor\$1 with parallel) and ("same" with state).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/10 10:52
L10	9	365/158,50,154,171,173,189.01. ccls. and MRAM and magneto-resistance and (transistor\$1 with parallel) and ("same" with state) .	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/10 10:53
L12	1	magneto-resistance same (conductive adj2 line) and (transistor\$1 with parallel) and ("same" with state)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/10 10:54
L13	1	(first near5 second near5 ferromagnetic) same tunnel same (first with conductive) same (second with conductive) and (transistor\$1 with parallel) and ("same" with state)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/10 10:57
L14	7	(first with ferromagnetic) and tunnel and (first with conductive) and (second with conductive) and (transistor\$1 with parallel) and ("same" with state)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/10 10:58
L17	6	(first near5 second near5 ferromagnetic) same tunnel same (first with conductive) same (second with conductive) same parallel	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/10 11:35
L18	1	(first near5 second near5 ferromagnetic) same tunnel same (first with conductive) same (second with conductive) same parallel.clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/10 11:05

L19	4	365/158,50,154,171,173,189.01. ccls. and (first with ferromagnetic) and tunnel and (first with conductive) and (second with conductive) and (transistor\$1 with parallel) and ("same" with state)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/10 11:09
L20	7	(first with ferromagnetic) and tunnel and (first with conductive) and (second with conductive) and (transistor\$1 with parallel) and ("same" with state)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/10 11:35
L21	5	365/158,50,154,171,173,189.01. ccls. and MRAM and magneto-resistance adj2 element\$1 and (transistor\$1 with parallel) and ("same" with state)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/10 11:10
L22	5	MRAM and magneto-resistance adj2 element\$1 and (transistor\$1 with parallel) and ("same" with state).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/10 11:11
L23	495	MRAM and (magnetic adj2 memory adj2 cell) and transistor\$1	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/10 11:21
L24	22	MRAM and (magnetic adj2 memory adj2 cell) and transistor\$1 and (transistor\$1 with parallel) and ("same" with state)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/10 11:33
L25	609	(transistor\$1 with parallel) and ("same" with state).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/10 11:23
L26	39	(transistor\$1 with parallel) same ("same" with state).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/10 11:23
L27	10	365/158,50,154,171,173,189.01. ccls. and MRAM and (magnetic adj2 memory adj2 cell) and transistor\$1 and (transistor\$1 with parallel) and ("same" with state)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/10 11:33
S1	410	(first with ferromagnetic) and tunnel and (first with conductive) and (second with conductive)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/10 10:58

S2	100	(first with ferromagnetic) same tunnel same (first with conductive) same (second with conductive)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/12 08:34
S3	48	(first near5 second near5 ferromagnetic) same tunnel same (first with conductive) same (second with conductive)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/10 11:02
S4	4	(first near5 second near5 ferromagnetic) same tunnel same (first with conductive) same (second with conductive) same transistor\$1	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/04 14:20
S5	2	ferromagnetic same tunnel same conductive same transistor\$1 same parallel	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/04 14:23
S6	3	(first near5 second near5 ferromagnetic) same tunnel same (first with conductive) same (second with conductive) and (transistor\$1 near5 parallel)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/04 14:29
S7	2	"6,269018".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/04 14:29
S8	2	"5,978257".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/04 14:30
S9	2	"5,699293".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/04 14:32
S10	2	"6,331943".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/04 14:32
S21	17	(first with (ferromagnetic or FM)) and tunnel and ((first with conductive) near5 dispose\$1) and (second with conductive)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/07 09:51

S22	1	(first with (ferromagnetic or FM)) and tunnel and ((first with conductive) near5 dispose\$1) and (second with conductive) same transistor\$1	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/07 09:53
S23	5	(first with (ferromagnetic or FM)) and tunnel and ((first with conductive) near5 dispose\$1) and (second with conductive) and transistor\$1	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/07 09:58
S24	10	("20020036877"   "20020097534"   "20020853319"   "5874886"   "6110751"   "6312840"   "6313973"   "6348274"   "6376337"   "6462641"   "6480412").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2005/03/07 09:59
S25	5	(first with (ferromagnetic or FM)) and tunnel and ((first with conductive) near5 dispose\$1) and transistor\$1	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/07 09:59
S26	150	(first with (ferromagnetic or FM)) and tunnel and (first with conductive) and transistor\$1	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/07 09:59
S27	19	(first with (ferromagnetic or FM)) and tunnel and (first with conductive) and (transistor\$1 near5 parallel)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/07 10:10
S28	9	("3892051"   "4259661"   "5226014"   "5258958"   "5285291"   "5410509"   "5508960"   "5793697"   "6314014").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2005/03/07 10:08
S29	17	(first with (ferromagnetic or FM)) and tunnel and (first with conductive) and pin\$4 and (transistor\$1 near5 parallel)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/07 10:10
S30	5	("5659499"   "5940319"   "6351408"   "6538297"   "6555858").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2005/03/07 10:13
S31	16	("6351408").URPN.	USPAT	OR	OFF	2005/03/07 10:15
S32	3	("4780848"   "5039655"   "5343422").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2005/03/07 10:33
S33	3	("5329486"   "5640343"   "5768181").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2005/03/07 10:34

S34	5	("5659499"   "5940319"   "6351408"   "6538297"   "6555858").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2005/03/07 10:44
S36	1	(tunnel\$3 with cell\$1) same state\$1 same (first near5 second) same (conductive adj2 line\$1) same change	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/07 11:36
S37	10	("4731757"   "5251170"   "5343422"   "5640343"   "5734606"   "5757695"   "5768181"   "5792569"   "5793693"   "5828598").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2005/03/07 11:05
S38	10	("4731757"   "5251170"   "5343422"   "5640343"   "5734606"   "5757695"   "5768181"   "5792569"   "5793693"   "5828598").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2005/03/07 11:08
S39	10	("5828598").URPN.	USPAT	OR	OFF	2005/03/07 11:08
S40	10	("5734605"   "5828598"   "5841692"   "5966012"   "6028786"   "6166948"   "6172904"   "6205053"   "6646910"   "6689622").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2005/03/07 11:08
S41	1	(tunnel\$3 with cell\$1) same (first near5 second) same (conductive adj2 line\$1) same change	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/07 11:36
S42	15	(tunnel\$3 with cell\$1) and (first near5 second) and (conductive adj2 line\$1) and change and (third adj2 conductive adj2 line)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/07 11:37
S43	14	365/158,185.13,185.23,104.ccls. and (first with ferromagnetic) same tunnel same (first with conductive) same (second with conductive)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/12 08:58
S46	118	365/158,50,154,171,173,189.01. ccls. and (first with ferromagnetic) and tunnel and (first with conductive) and (second with conductive)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/10 11:08
S47	26	365/158,50,154,171,173,189.01. ccls. and (first with ferromagnetic) same tunnel same (first with conductive) same (second with conductive)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/14 09:37

S49	56	365/158,50,154,171,173,189.01. ccls. and (spin-dependent with tunnel\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/14 09:47
S50	9	365/158,50,154,171,173,189.01. ccls. and (spin-dependent with tunnel\$3) and magneto-resistance	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/14 09:39
S51	202	365/158,50,154,171,173,189.01. ccls. and MRAM and magneto-resistance	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/10 10:53
S52	51	365/158,50,154,171,173,189.01. ccls. and MRAM and magneto-resistance same spin	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/10 10:53
S53	5	365/158,50,154,171,173,189.01. ccls. and MRAM and magneto-resistance same ((spin-dependent adj2 tunnel\$3) or SDT)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/14 09:44
S54	9	("20030007398"   "6163477"   "6385082"   "6504221"   "6535416"   "6603678"   "6728132"   "6781910"   "6819587").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2005/03/14 09:43
S55	7	("6005800"   "6104633"   "6130814"   "6295225"   "6368878"   "6590750"   "6740947").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2005/03/14 09:43
S56	94	365/158,50,154,171,173,189.01. ccls. and MRAM and magneto-resistance adj2 element\$1	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/10 11:09
S57	7	365/158,50,154,171,173,189.01. ccls. and MRAM and magneto-resistance adj2 element\$1 same spin	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/14 09:45
S58	2	"6,775183".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/14 09:47